

Support Information:

Strain-tuned optoelectronic property of Hollow Gallium sulfides microsphere

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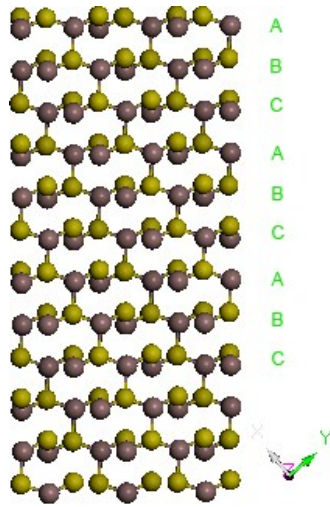


Figure S1. The crystal structure of Ga_2S_3 . The stack sequence is ABC type along $[110]$ axis.

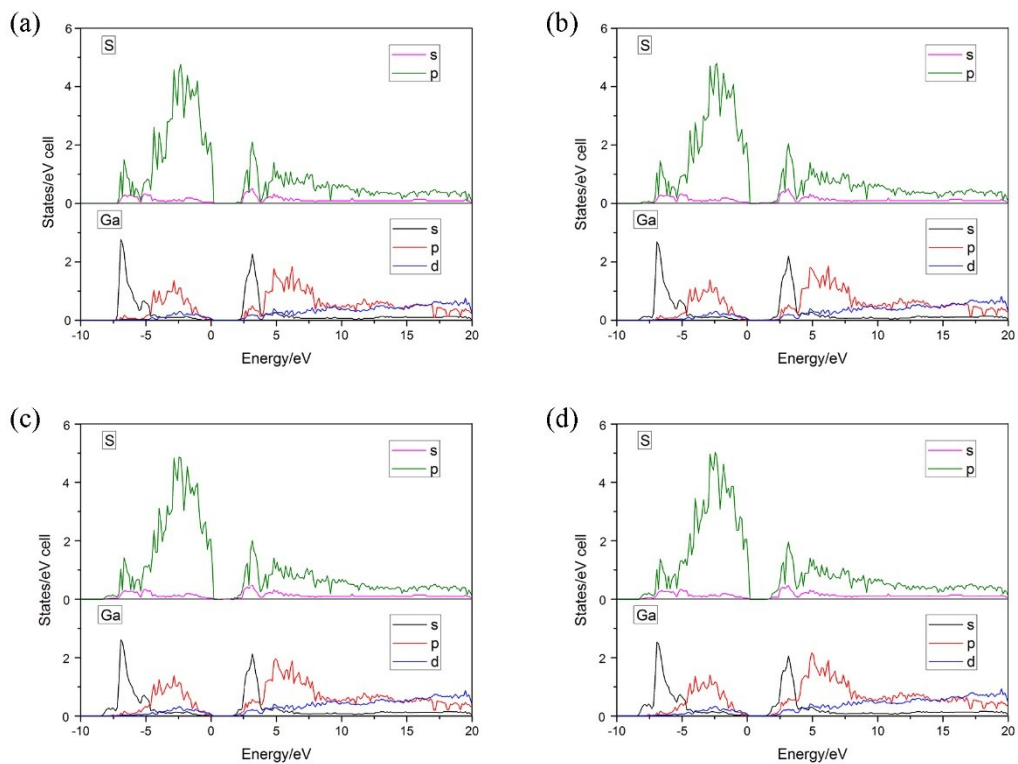


Figure S2. The calculated DOS of samples at (a) 950 °C, (b) 900 °C, (c) 850 °C, (d) 800°C.

With the increasing of growth temperature, the Ga-4p and S-3s state of the conduction regions shift towards the low energy area.